FAIRCHILD SEMICONDUCTOR®

November 2001

IRF614B/IRFS614B

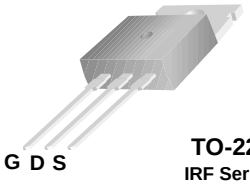
250V N-Channel MOSFET

General Description

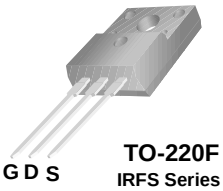
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

Features

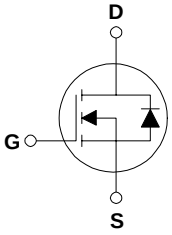
- 2.8A, 250V, $R_{DS(on)}$ = 2.0Ω @V_{GS} = 10 V
- Low gate charge (typical 8.1 nC)
- Low Crss (typical 7.5 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-220
IRF Series



TO-220F
IRFS Series



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		IRF614B	IRFS614B	Units
V_{DSS}	Drain-Source Voltage		250		V
I_D	Drain Current - Continuous (T_C = 25°C)		2.8	2.8 *	A
	- Continuous (T_C = 100°C)		1.8	1.8 *	A
I_{DM}	Drain Current - Pulsed	(Note 1)	8.5	8.5 *	A
V_{GSS}	Gate-Source Voltage		± 30		V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	45		mJ
I_{AR}	Avalanche Current	(Note 1)	2.8		A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	4.0		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5		V/ns
P_D	Power Dissipation (T_C = 25°C)		40	22	W
	- Derate above 25°C		0.32	0.18	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300		°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	IRF614B	IRFS614B	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case Max.	3.14	5.58	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient Max.	62.5	62.5	°C/W

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Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	250	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.26	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 250 V, V_{GS} = 0 V	--	--	10	μA
		V_{DS} = 200 V, T_C = 125°C	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 1.4 A	--	1.49	2.0	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 1.4 A (Note 4)	--	2.5	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	210	275	pF
C_{oss}	Output Capacitance		--	35	45	pF
C_{rss}	Reverse Transfer Capacitance		--	7.5	10	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 125 V, I_D = 2.8 A, R_G = 25 Ω (Note 4, 5)	--	6.0	22	ns
t_r	Turn-On Rise Time		--	30	70	ns
$t_{d(off)}$	Turn-Off Delay Time		--	25	60	ns
t_f	Turn-Off Fall Time		--	30	70	ns
Q_g	Total Gate Charge	V_{DS} = 200 V, I_D = 2.8 A, V_{GS} = 10 V (Note 4, 5)	--	8.1	10.5	nC
Q_{gs}	Gate-Source Charge		--	1.4	--	nC
Q_{gd}	Gate-Drain Charge		--	3.5	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	2.8	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	8.5	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.8 A	--	--	1.5	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 2.8 A, dI_F / dt = 100 A/μs (Note 4)	--	130	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.49	--	μC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 9.2mH, I_{AS} = 2.8A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. $I_{SD} \leq$ 2.8A, di/dt $\leq$ 300A/μs, $V_{DD} \leq BV_{DSS,}$ Starting T_J = 25°C
4. Pulse Test : Pulse width $\leq$ 300μs, Duty cycle $\leq$ 2%
5. Essentially independent of operating temperature

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Typical Characteristics

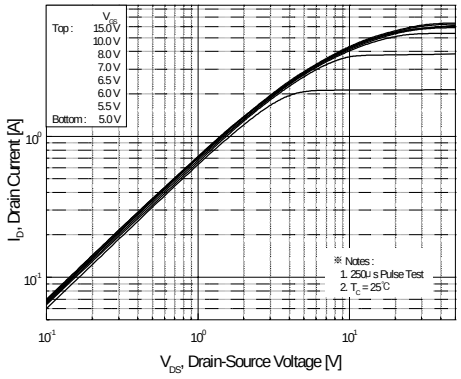

Figure 1. On-Region Characteristics

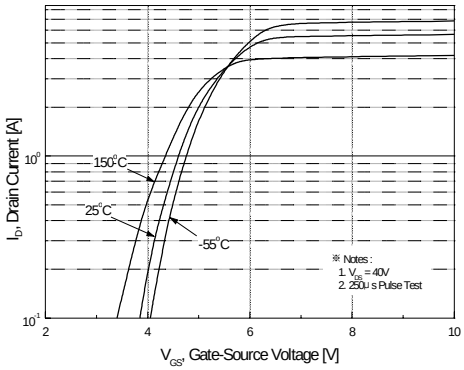

Figure 2. Transfer Characteristics

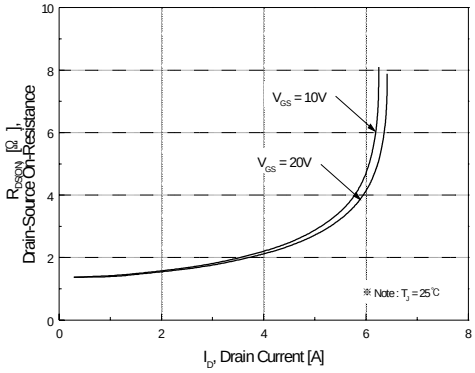

Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

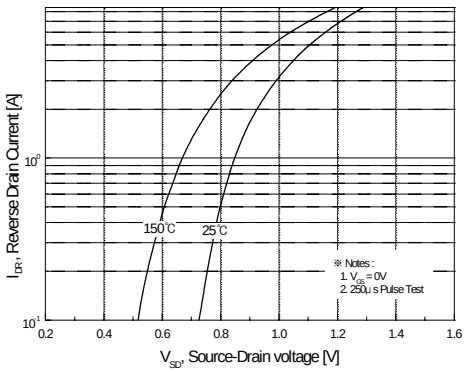

Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

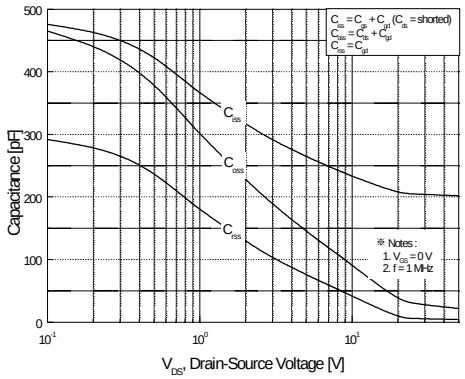

Figure 5. Capacitance Characteristics

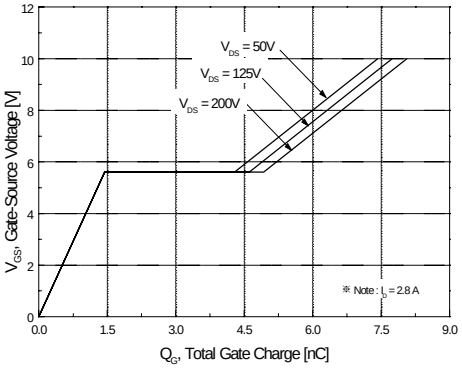

Figure 6. Gate Charge Characteristics

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Typical Characteristics (Continued)

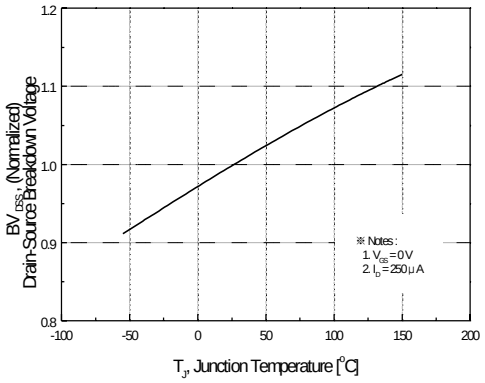

Figure 7. Breakdown Voltage Variation vs Temperature

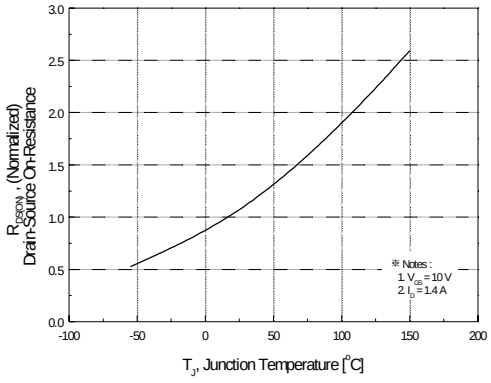

Figure 8. On-Resistance Variation vs Temperature

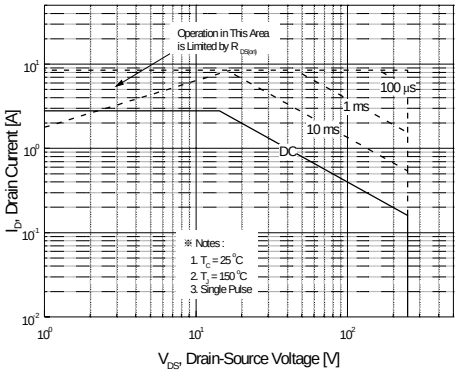

Figure 9-1. Maximum Safe Operating Area for IRF614B

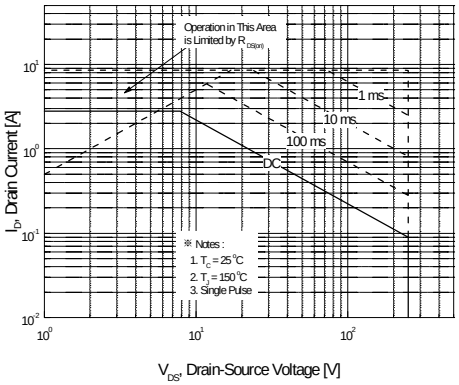

Figure 9-2. Maximum Safe Operating Area for IRFS614B

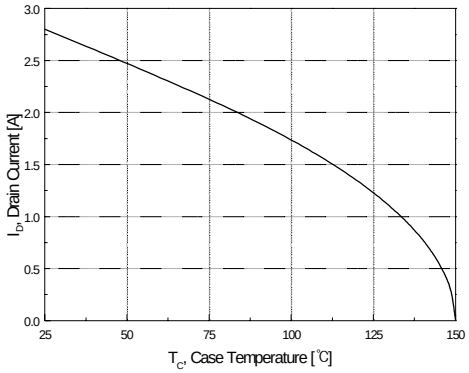

Figure 10. Maximum Drain Current vs Case Temperature

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Typical Characteristics (Continued)

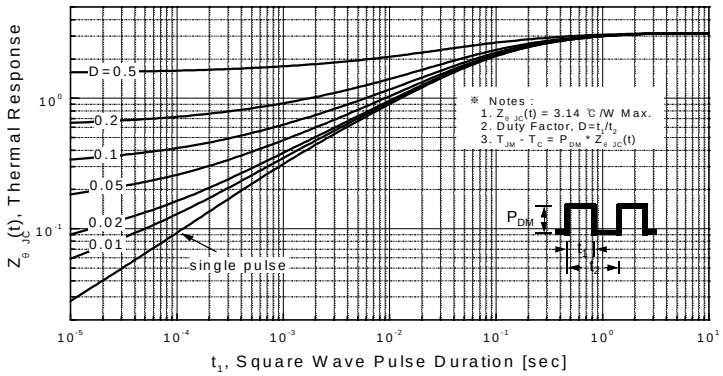

Figure 11-1. Transient Thermal Response Curve for IRF614B

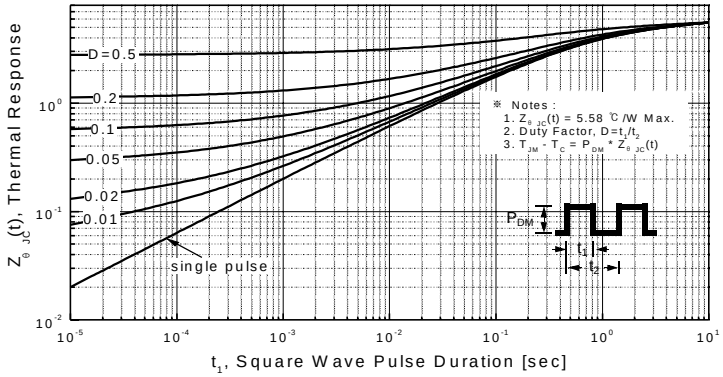

Figure 11-2. Transient Thermal Response Curve for IRFS614B

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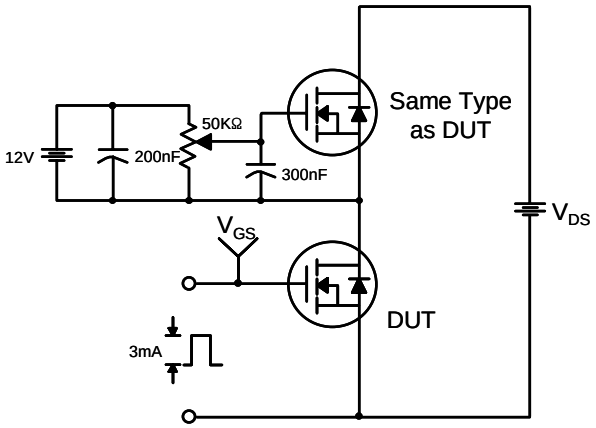
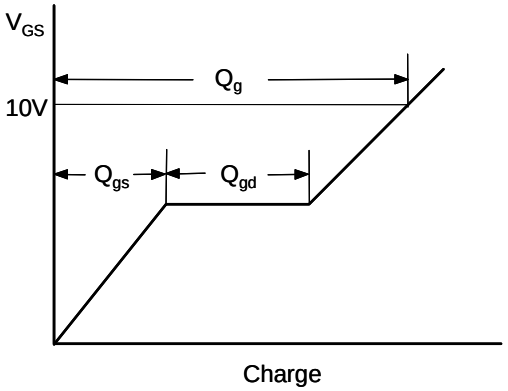
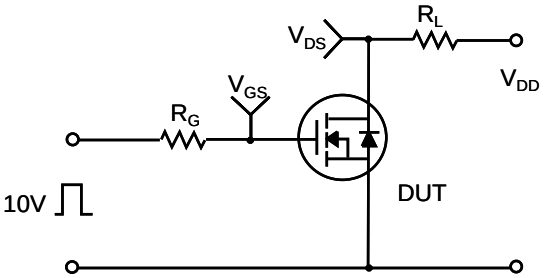
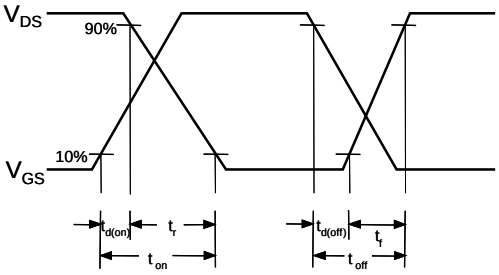
Gate Charge Test Circuit & Waveform



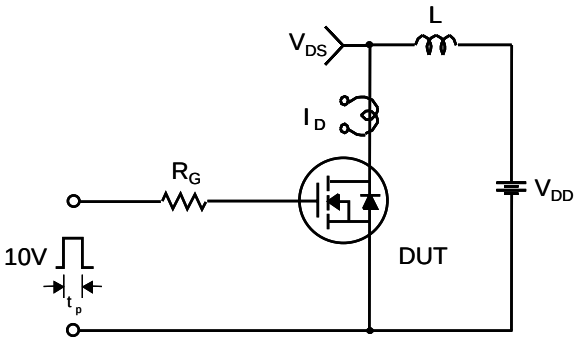


Resistive Switching Test Circuit & Waveforms

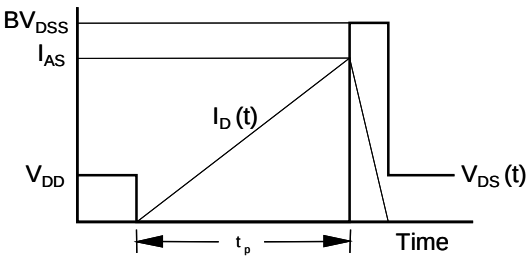




Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



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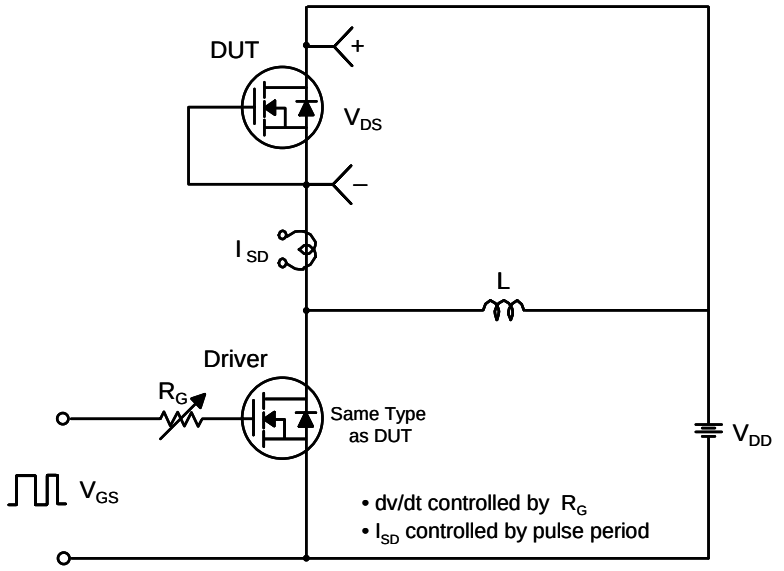
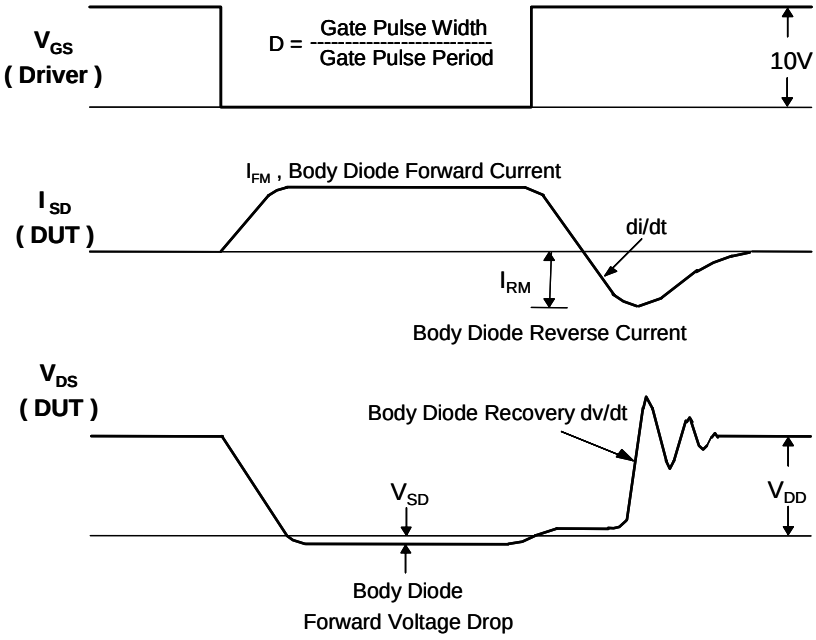
Peak Diode Recovery dv/dt Test Circuit & Waveforms





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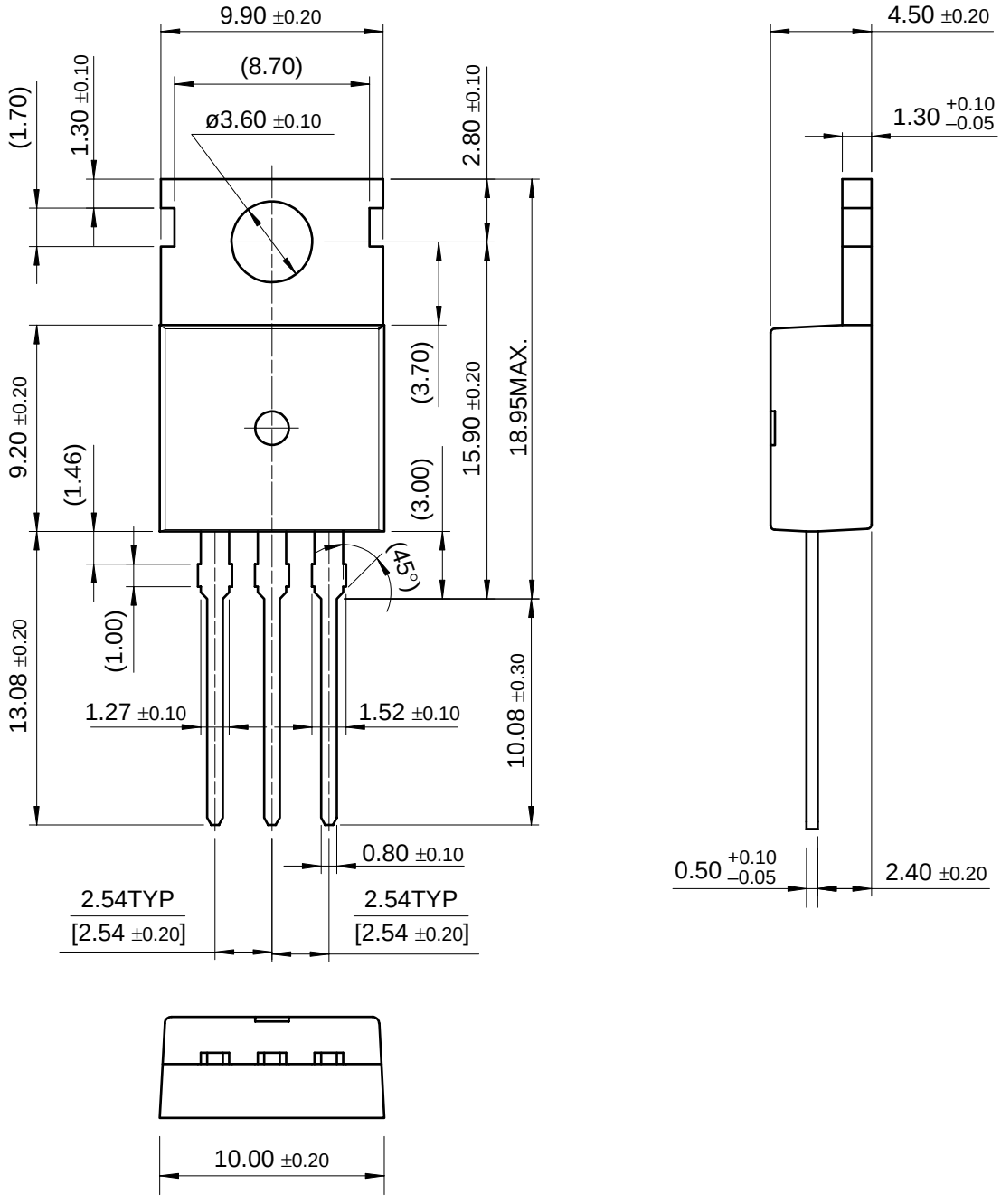
Package Dimensions

TO-220



Dimensions in Millimeters

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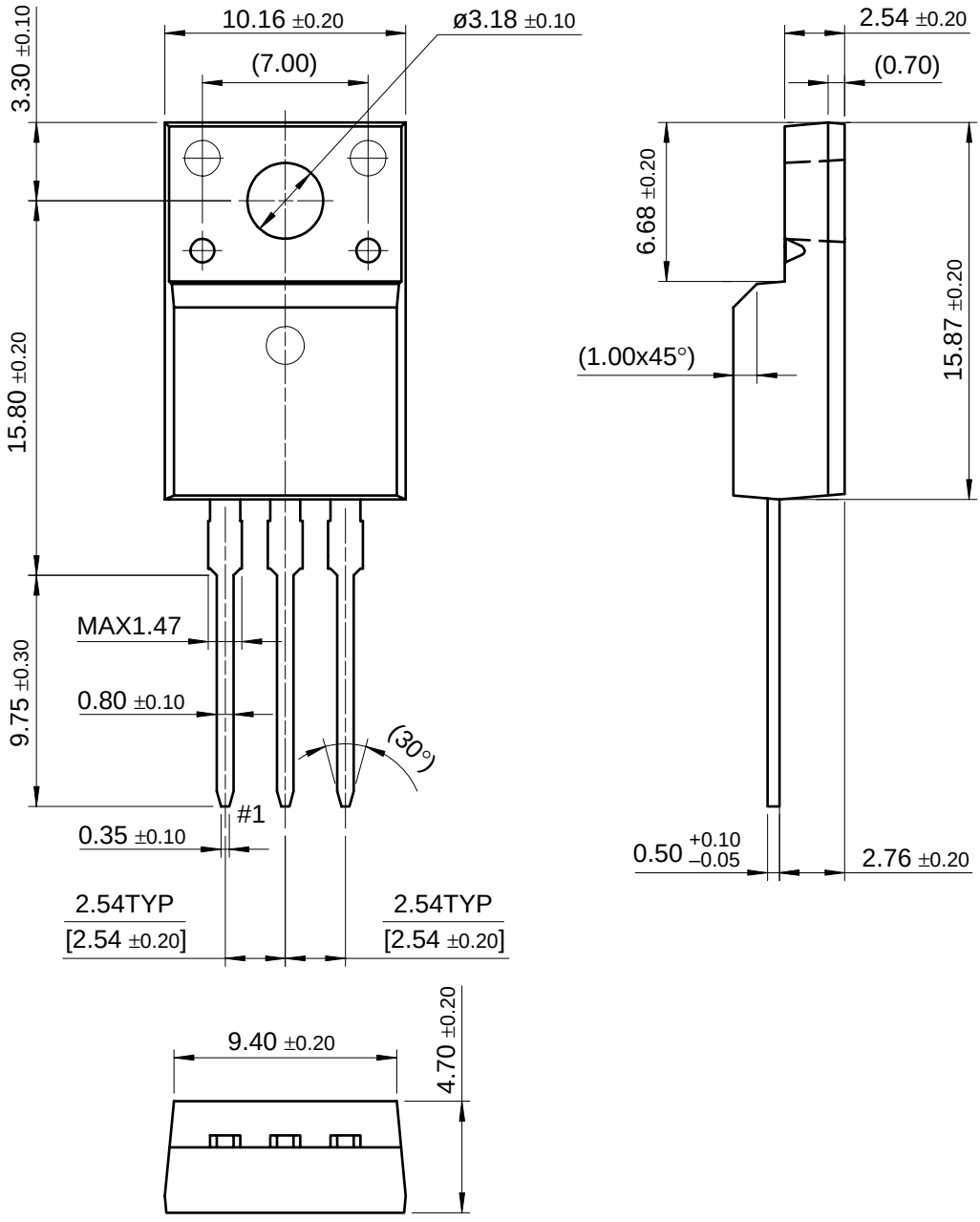
Package Dimensions (Continued)

TO-220F



Dimensions in Millimeters

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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IRFS614B

250V N-Channel B-FET / Substitute of IRFS614 & IRFS614A

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General description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

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- Low Crss (typical 7.5 pF)
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- 100% avalanche tested
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Product status/pricing/packaging

BUY

Product	Product status	Pb-free Status	Package type	Leads	Packing method	Package Marking Convention**
IRFS614B_FP001	Not recommended for new designs		TO-220F	3	RAIL	Line 1: **$Y** (Fairchild logo) &**Z** (Asm. Plant Code) &**4** (4-Digit Date Code) Line 2: IRFS Line 3: 614B

Indicates product with Pb-free second-level interconnect. For more information click here.

Package marking information for product IRFS614B is available. Click here for more information .

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Qualification Support

Click on a product for detailed qualification data

Product
IRFS614B_FP001

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